Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!

Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832
Email & Skype: info@chipsmall.com Web: www.chipsmall.com
Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China

IXYS

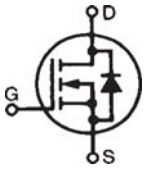
Advance Technical Information

High Voltage Power MOSFETs

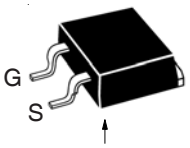
IXTA02N450HV
IXTT02N450HV

V_{DSS} = 4500V
I_{D25} = 200mA
$R_{DS(on)}$ ≤ 750Ω

N-Channel Enhancement Mode



TO-263 (IXTA)



TO-268 (IXTT)

G = Gate D = Drain
S = Source Tab = Drain

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	T_J = 25°C to 150°C	4500	V
V_{DGR}	T_J = 25°C to 150°C, R_{GS} = 1MΩ	4500	V
V_{GSS}	Continuous	±20	V
V_{GSM}	Transient	±30	V
I_{D25}	T_C = 25°C	200	mA
I_{DM}	T_C = 25°C, Pulse Width Limited by T_{JM}	600	mA
P_D	T_C = 25°C	113	W
T_J		- 55 ... +150	°C
T_{JM}		150	°C
T_{stg}		- 55 ... +150	°C
T_L	1.6mm (0.062 in.) from Case for 10s	300	°C
T_{SOLD}	Plastic Body for 10 seconds	260	°C
F_C	Mounting Force (TO-263)	10..65 / 22..14.6	N/lb
Weight	TO-263	2.5	g
	TO-268	4.0	g

Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	4.0		6.5	V
I_{GSS}	V_{GS} = ±20V, V_{DS} = 0V			±100	nA
I_{DSS}	V_{DS} = 3.6kV, V_{GS} = 0V			5	μA
	V_{DS} = 4.5kV			10	μA
	V_{DS} = 3.6kV T_J = 100°C		25		μA
$R_{DS(on)}$	V_{GS} = 10V, I_D = 10mA, Note 1			750	Ω

Features

- High Blocking Voltage
- High Voltage Packages

Advantages

- Easy to Mount
- Space Savings
- High Power Density

Applications

- High Voltage Power Supplies
- Capacitor Discharge Applications
- Pulse Circuits
- Laser and X-Ray Generation Systems

Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
g_{fs}	V_{DS} = 60V, I_D = 30mA, Note 1	60	100		mS
C_{iss}	V_{GS} = 0V, V_{DS} = 25V, f = 1MHz		256		pF
C_{oss}			19		pF
C_{rss}			5.5		pF
R_{Gi}	Gate Input Resistance		76		Ω
$t_{d(on)}$	**Resistive Switching Times**		17		ns
t_r	V_{GS} = 10V, V_{DS} = 500V, I_D = 0.5 • I_{D25}		48		ns
$t_{d(off)}$	R_G = 10Ω (External)		28		ns
t_f			143		ns
$Q_{g(on)}$	V_{GS} = 10V, V_{DS} = 1kV, I_D = 0.5 • I_{D25}		10.4		nC
Q_{gs}			3.4		nC
Q_{gd}			5.0		nC
R_{thJC}				1.1	°C/W

Source-Drain Diode

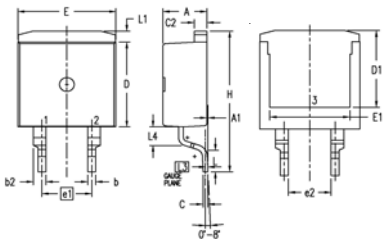
Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
I_S	V_{GS} = 0V			200	mA
I_{SM}	Repetitive, Pulse Width Limited by T_{JM}			800	mA
V_{SD}	I_F = I_S, V_{GS} = 0V, Note 1			1.5	V
t_{rr}	I_F = 200mA, -di/dt = 50A/μs, V_R = 100V		1.6		μs

Note: 1. Pulse test, t ≤ 300μs, duty cycle, d ≤ 2%.

ADVANCE TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

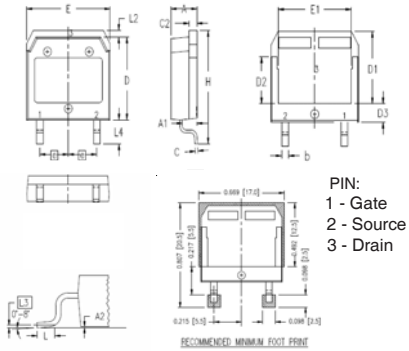
TO-263 (VHV) Outline



PIN: 1 - Gate
2 - Source
3 - Drain

SYM	INCHES MIN	INCHES MAX	MILLIMETER MIN	MILLIMETER MAX
A	.170	.185	4.30	4.70
A1	.000	.008	0.00	0.20
A2	.091	.098	2.30	2.50
b	.028	.035	0.70	0.90
b2	.046	.054	1.18	1.38
C	.018	.024	0.45	0.60
C2	.049	.055	1.25	1.40
D	.354	.370	9.00	9.40
D1	.311	.327	7.90	8.30
E	.386	.402	9.80	10.20
E1	.307	.323	7.80	8.20
e1	.200 BSC		5.08 BSC	
(e2)	.163	.174	4.13	4.43
H	.591	.614	15.00	15.60
L	.079	.102	2.00	2.60
L1	.039	.055	1.00	1.40
L3	.010 BSC		0.254 BSC	
(L4)	.071	.087	1.80	2.20

TO-268 (VHV) Outline



PIN:
1 - Gate
2 - Source
3 - Drain

SYM	INCHES MIN	INCHES MAX	MILLIMETER MIN	MILLIMETER MAX
A	.193	.201	4.90	5.10
A1	.106	.114	2.70	2.90
A2	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
C	.016	.026	0.40	0.65
C2	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D1	.465	.476	11.80	12.10
D2	.295	.307	7.50	7.80
D3	.114	.126	2.90	3.20
E	.624	.632	15.85	16.05
E1	.524	.535	13.30	13.60
e	.215 BSC		5.45 BSC	
H	.736	.752	18.70	19.10
L	.067	.079	1.70	2.00
L2	.039	.045	1.00	1.15
L3	.010 BSC		0.25 BSC	
L4	.150	.161	3.80	4.10

Fig. 1. Output Characteristics @ T_J = 25ºC

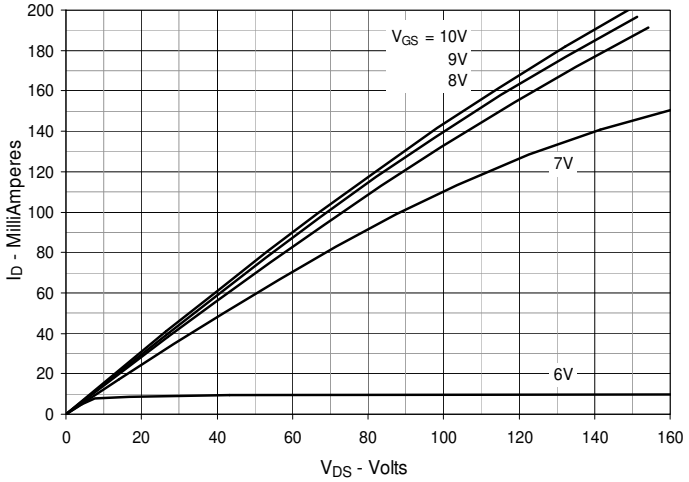


Fig. 2. Extended Output Characteristics @ T_J = 25ºC

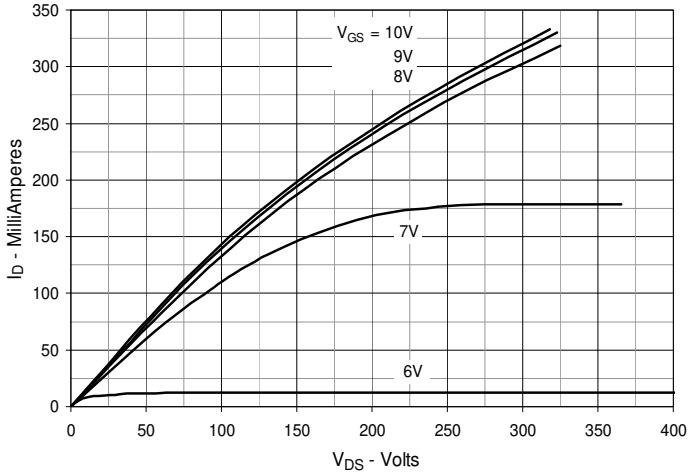


Fig. 3. Output Characteristics @ T_J = 125ºC

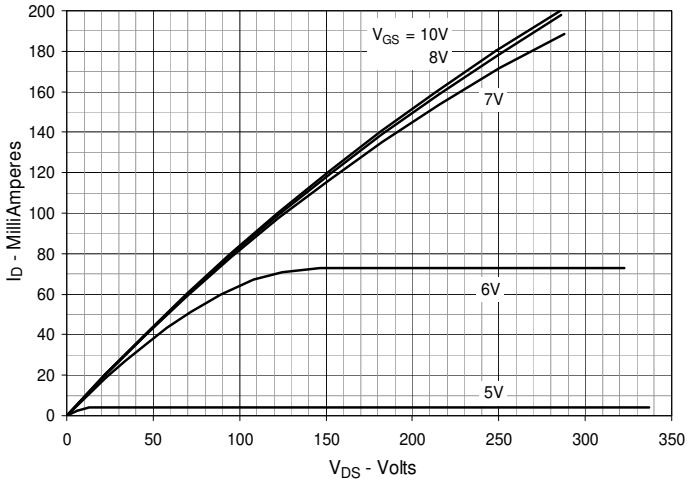


Fig. 4. $R_{DS(on)}$ Normalized to I_D = 100mA Value vs. Junction Temperature

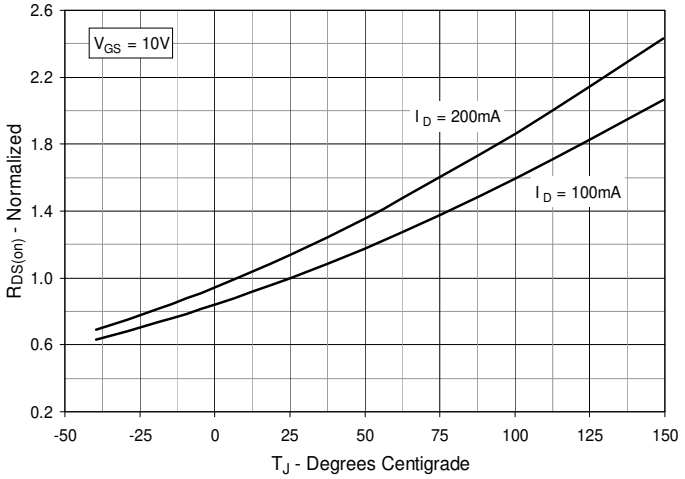


Fig. 5. $R_{DS(on)}$ Normalized to I_D = 100mA Value vs. Drain Current

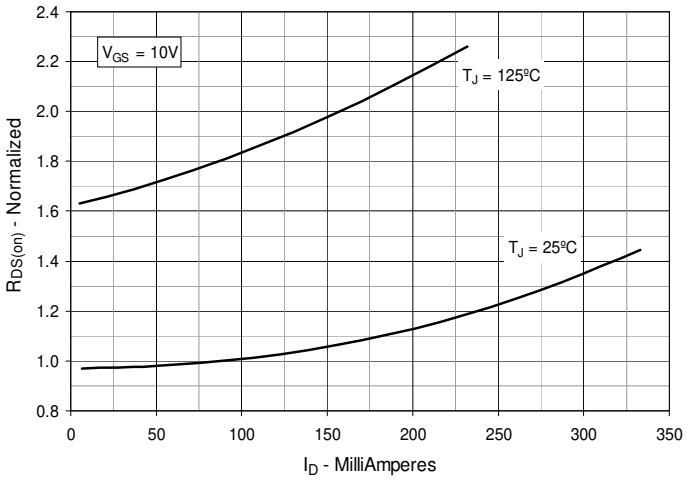


Fig. 6. Maximum Drain Current vs. Case Temperature

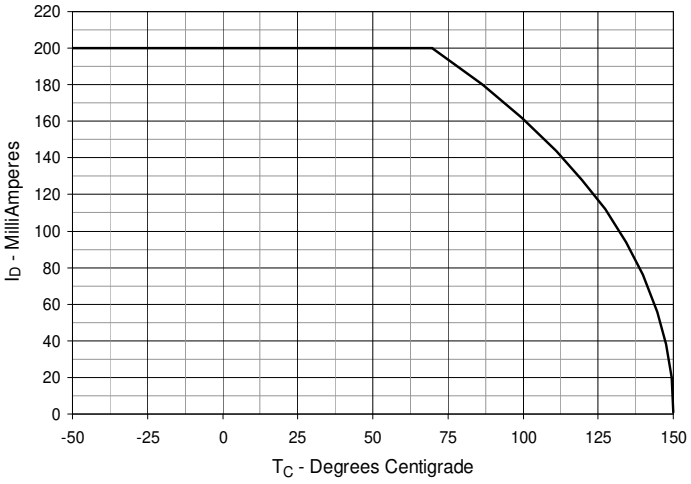


Fig. 7. Input Admittance

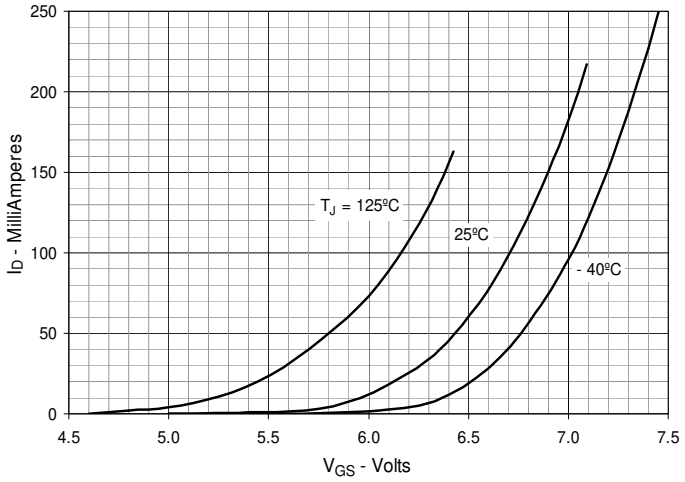


Fig. 8. Transconductance

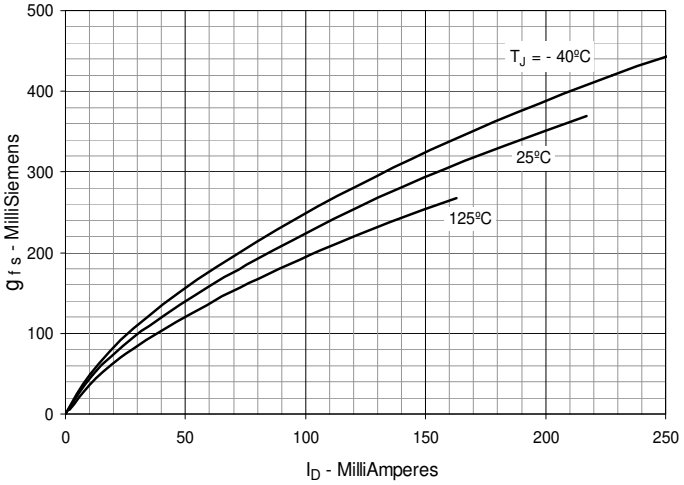


Fig. 9. Forward Voltage Drop of Intrinsic Diode

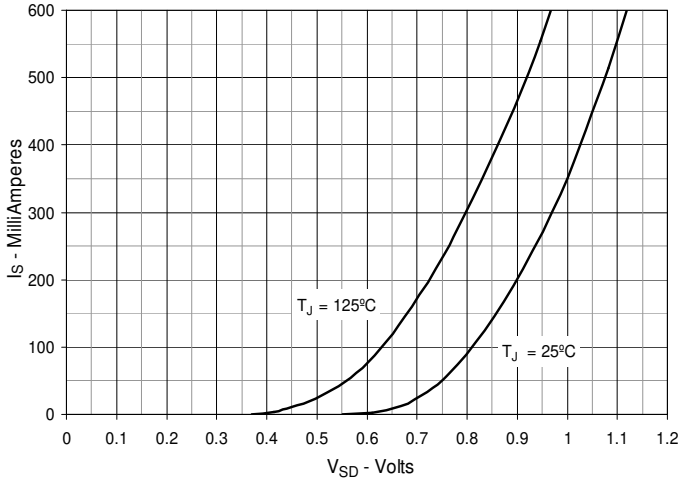


Fig. 10. Gate Charge

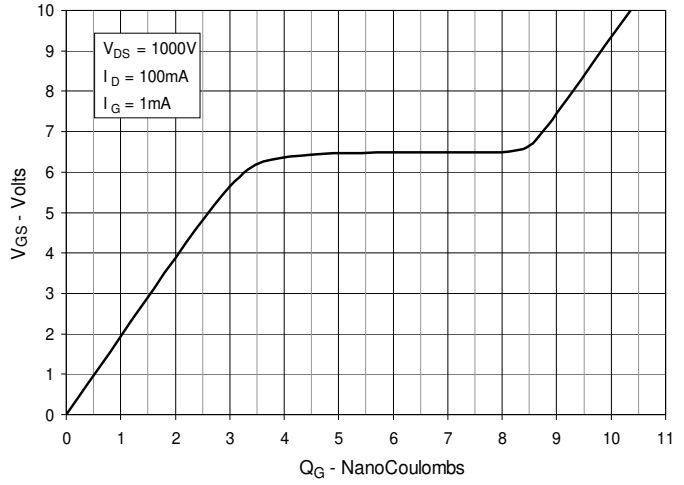


Fig. 11. Capacitance

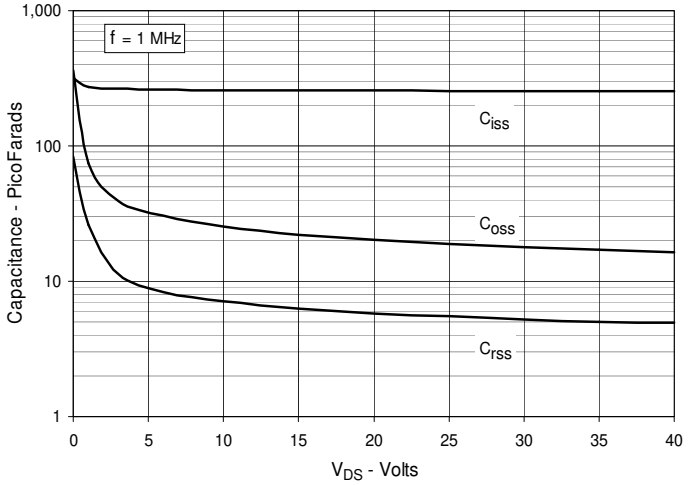


Fig. 12. Maximum Transient Thermal Impedance

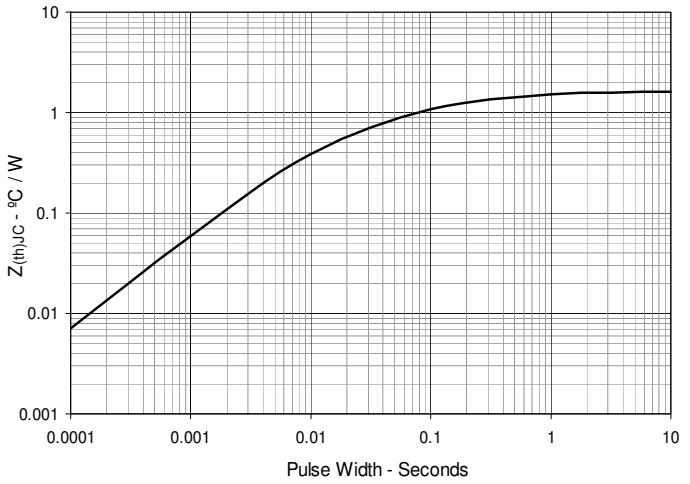


Fig. 13. Forward-Bias Safe Operating Area @ T_C = 25ºC

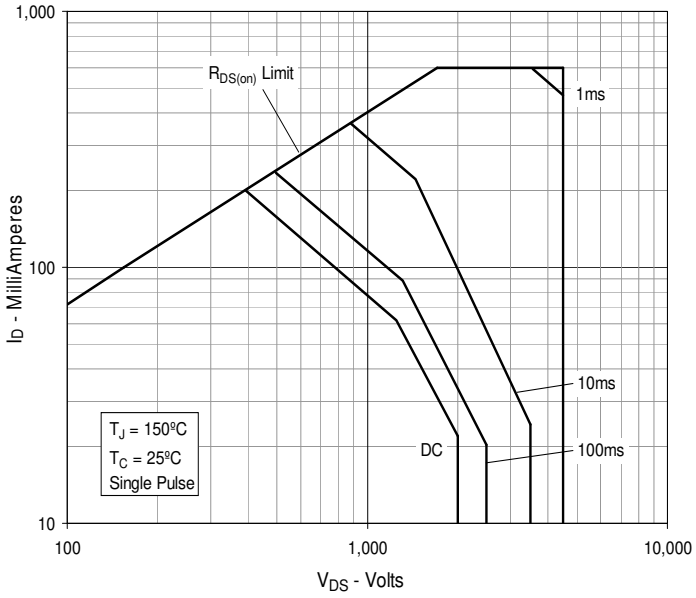


Fig. 14. Forward-Bias Safe Operating Area @ T_C = 75ºC